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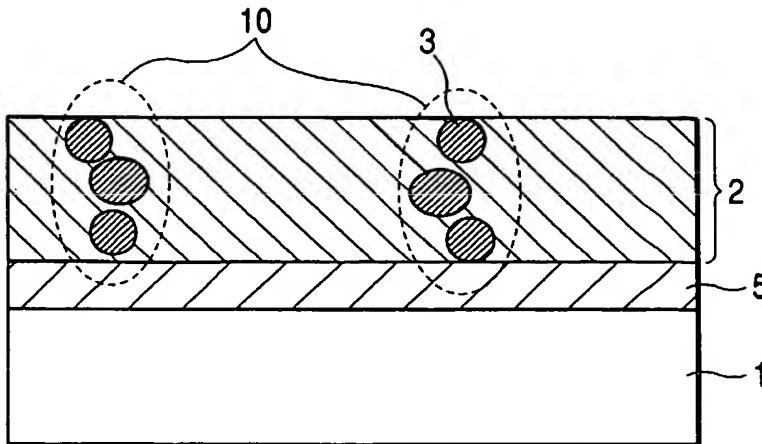
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(54) Title: ELECTRON-EMITTING DEVICE AND MANUFACTURING METHOD THEREOF



(57) **Abstract:** There is provided an electron-emitting device of a field emission type, with which the spot size of an electron beam is small, an electron emission area is large, highly efficient electron emission is possible with a low voltage, and a manufacturing process is easy. The electron-emitting device includes a layer 2 which is electrically connected to a cathode electrode 5, and a plurality of particles 3 which contains a material having resistivity lower than that of a material constituting the layer 2, and is wherein a density of particles 3 in the layer 2 is $1 \times 10^{14}/\text{cm}^3$ or more and $5 \times 10^{18}/\text{cm}^3$ or less.